Course	se 18ECC102J	C102J	Course	ELECTRONIC DEVICES	Course Category	O				Profe	Professional Core	/ Core				3 L	⊢ 0	2	O 4
Pre-re Cou	Pre-requisite 18EE Courses	18EES101J		Co-requisite Nii Courses	Progressive Courses		18ECC	18ECC2011, 18ECC2021, 18ECE203T, 18ECE303T, 18ECE321T, 18ECE322T	SECC2	327, 1E	3ECE2	03T, 1 _k	3ECE3	03T, 1 ₈	SECE3	21T, 1	8ECE	322T	
Course	Course Offering Department	rtment	Electronic	Electronics and Communication Engineering Data Book / Codes/Standards	Nil														
Course	Learning Ratio	onale (CLR): The purpo	Course Learning Rationale (CLR): The purpose of learning this course is to:	Lear	Learning				-	rograr	n Lear	Program Learning Outcomes (PLO)	utcom	les (PI	o,			
CLR 1	Provide a bas	sis for unde	erstanding sem	CLR-1: Provide a basis for understanding semiconductor material, how a pn junction is formed and its principle of operation	1	2 3	_	1 2	က	4	5	2 9	∞	6	10	11 12	2 13	14	15
CLR-2:	Explain the ir Discuss the t	mportance basic chara	of diode in elec	CLR-2: Explain the importance of diode in electronic circuits by presenting appropriate diode applications CLR-3: Discuss the basic characteristics of several other types of diodes that are designed for specific applications													tneme	ţue	цα
CLR-4:	Describe the	basic struc	ture, operation	CLR4: Describe the basic structure, operation and characteristics of BJT, and discuss its use as a switch and an amplifier.	- 10	- 0				иср		vtilid					vəid	ewe	96910
CLR-5:	Describe the	basic struc	ture, operation	CLR-5: Describe the basic structure, operation and characteristics of MOSFET, and discuss its use as a switch and an amplifier.	nool	- 2 2		әбр	ţuə	eəse		enis		Nork		901	oA li	1usg	Вез
CLR-6:		engineerinຸ s used by te	g tools such as chnicians and	Use modern engineering tools such as PSPICE to c <mark>arr</mark> y out de <mark>sign ex</mark> periments a <mark>nd ga</mark> in ex <mark>per</mark> ience with instruments and methods used by technicians and electronic eng <mark>ine</mark> ers	20020					A ,ngi				V msə				ject Ma	alyze &
										eed ,				T & le		_			
Course	Learning Outco	comes (CLC	At the enα	Course Learning Outcomes (CLO): At the end of this course, learners will be able to:	Level of	Expecte		eenign∃ Problem	3 ngisəQ	sisylsnA	Modern	Society 8	Ethics	subivibnl	inmmo0	Project M Life Long	PSO_1:	S – OS9 pindoeT	6 – OSd
CL0-1:	Explain the o	peration, ci	haracteristics, _I	CLO-1: Explain the operation, characteristics, parameters and specifications of semiconductor diodes and special diodes	9 1					c			ı				- 1	•	,
CL0-2:	Illustrate impo	ortant appli	ications of sem	CLO-2: Illustrate important applications of semiconductor diodes and special diodes.	2 6	02 09		1			1		•				-	1	,
CL0-3:		lar transisto g.	or construction,	Review bipolar transistor construction, operation, characteristics and parameters, as well as its application in ampfification and switching.	-	02 09		- Н	1	i.			ř			- W	-	1	1
CL0-4:		effect trans and switch.	sistor constructing.	Review field-effect transistor construction, operation, characteristics and parameters, as well as its application in amplification and switching.	1 6	02 09		H	1	í	ř		ı			- -	_	7	-
CL0-5:	Construct a c	circuit, then	make function	CLO-5: Construct a circuit, then make functional measurements to understand the operating characteristics of the device / circuit	8	70 75		1	ī	ī	H		4	ı		<u>'</u>	7	7	,
CLO-6:	Solve specific	ic design pr	oblem, which a	CLO-6: Solve specific design problem, which after completion will be verified using modern engineering tools such as PSPICE.	2 7	70 75	ш	1	T		H		7	Н	N	- M	- 1	٠	٠

2	Duration	Semiconductor Diodes	Diode Circuits	Special Diodes	Bipolar Junction Transistors	MOS Field-Effect Transistors
= 	(hour)	15	15	15	15	15
2	SLO-1	Basic semiconductor theory: Intrinsic & extrinsic semiconductors	HWR operation, Efficiency and ripple factor Backward diode	Backward diode	Physical structure	Physical structure
<u>,</u>	SLO-2	SLO-2 Current flow in semiconductors	Problem solving	Varactor diode	Device operation of BJT	Device operation of E-MOSFET & D- MOSFET
,	SLO-1	SLO-1 PN junction theory: Equilibrium PN junction operation, Efficiency and ripple factor		Step recovery diode	Current-Voltage characteristics of CE BJT configuration	I-V characteristics of E-MOSFET
7	SLO-2	SLO-2 Forward biased PN junction	Problem solving	Point-contact diode	Current-Voltage characteristics of CE BJT Problem solving configuration	Problem solving
6.0	SLO-1	SLO-1 Reverse biased PN junction	Bridge FWR operation, Efficiency and hipple factor	Metal-semiconductor junction: Structure, Energy band diagram	Current-Voltage characteristics of CB BJT Derive drain current configuration	Derive drain current
3	SLO-2	SLO-2 Relation between Current and Voltage	ing	Forward & Reverse Characteristics of Schottky Diode	Current-Voltage characteristics of CB BJT configuration	Problem solving
S 4-5	SLO-1 SLO-2	SLO-1 Lab 1: PN Junction Diode Characteristics Lab 4: Diode clipping and clamping circuits Lab 7: Series and Shunt Regulators	Lab 4: Diode clipping and clamping circuits	Q.	Lab 10: BJT and MOSFET Switching Circuits	Lab 13: Repeat Experiments
ď	SLO-1	SLO-1 Calculate depletion width	Filters: Inductor & Capacitor Filters	Tunnel Diode	Current-Voltage characteristics of CC BJT Derive transconductance configuration	Derive transconductance
ř	SLO-2	SLO-2 Calculate barrier potential	Problem solving	Tunnel Diode	Current-Voltage characteristics of CC BJT Problem solving configuration	Problem solving
S-7		SLO-1 Derive diode current equation	Filters: LC & CLC Filters	Gunn Diode	BJT as an amplifier	CMOS FET

	SLO-2	SLO-2 Derive diode current equation	Problem solving	Gunn Diode	BJT as a switch	MOSFET as an amplifier
ď	·	SLO-1 Effect of Capacitance in PN junction: Transition Capacitance	Diode Clippers	IMPATT Diode	BJT circuit models – h-parameter	MOSFET as a switch
5		SLO-2 Diffusion Capacitance	Problem solving	IMPATT Diode	ВJT circuit models – hybrid-т parameter	Problem solving
s 9-10	SLO-1 SLO-2	S SLO-1 SLO-2 Lab 2: Zener diode characteristics	Lab 5: BJT Characteristics	Lab 8: MOSFET Characteristics	Lab 11: Photoconductive Cell, LED, and Solar Cell Characteristics	Lab-14: Model Examination
,	SLO-1	Energy band structure of PN Junction Diode	Diode Clampers	PIN Diode	BJT biasing circuits and stability analysis: Base bias and emitter bias	Biasing Circuits for MOSFET: Gate Bias
-6	SLO-2	Ideal diode and its current-voltage characteristics	Prob <mark>lem</mark> solving	PIN Photodiode	Problem solving	Problem Solving
		SLO-1 Terminal characteristics & parameters	Voltage Multipliers	Avalanche photodiode	Voltage-divider bias	Self-bias
7 -6		SLO-2 Diode modeling	Zener diode: Characteristics, breakdown mechanisms	Laser diode	Problem solving	Problem Solving
C 13		SLO-1 DC load line and analysis	Zener resistances and temperature effects Problem solving Zener diode as voltage regulator	Problem solving	Collector-feedback bias	Voltage-divider bias
2		SLO-2 Problem solving	Problem solving	Problem solving	Problem solving	Problem Solving
S 14-15	SLO-1	S SLO-1 14-15 SLO-2 Lab 3: Diode rectifier circuits	Lab 6: BJT Biasing Circuits	Lab 9: MOSFET Biasing Circuits	Lab 12: Simulation experiments using PSPICE	Lab 15: End-Semester Practical Examination

	1.	David A. Bell, Electronic Devices and Circuits, 5th ed., Oxford University Press, 2015	5.	Robert L.	5. Robert L. Boylestad, Louis Nashelsky, Electronic Devices and Circuit Theory, 11th ed., Pearson Education, 2013
Learning	2	Donald Neamen, Electronic Circuits: Analysis and Design, 3rd ed., McGraw-Hill Education, 2011 6.	1 6.	Muhamma	Muhammad Rashid, Microelectronic Circuits: Analysis & Design, 2 nd ed., Cengage Learning, 2010
Resources	ω.	ry and Applicati	4 7.	Muhamme	Auhammed H Rashid, Introduction to Pspice using OrCAD for circuits and electronics, 3 rd ed., Pearson, 2004
	4	Thomas L. Flovd, Electronic Devices", 9th ed., Pearson Education, 2013	φ.	Laboratory	Laboratory Manual, Department of ECE, SRM University

Learning Assessment	ment										
	2,000			Contir	nuous Learning Ass	Continuous Learning Assessment (50% weightage)	thtage)			in the state of th	(czc+dzicz /002)
	DIOUTH S	CLA-	CLA - 1 (10%)	CLA - 2 (15%)	2 (15%)	CLA-	CLA - 3 (15%)	CLA-4	CLA - 4 (10%)#	riliai Examinatio	rınaı Examınatıon (50% welginlaye)
	Level of Hilling	Theory	Practice	Theory	Practice	Theory	Practice	Theory	Practice	Theory	Practice
7 0:0	Remember	/000	/000	450/	150/	150/	1501	150/	450/	450/	450/
Level	Understand	20%	20%	13%	13%	13%	13%	10%	13%	13%	0,070
	Apply	/000	/906	/000	/006	/000	/000	/000	/000	/000	/000
Z level Z	Analyze	2070	0.707	0/07	2070	20.70	2070	20%	2070	60.70	0/07
c	Evaluate	4007	400/	450/	450/	450/	450/	4507	450/	450/	450/
Level 3	Create	10%	10%	0,07	13%	13%	13%	10%	13%	13%	0,07
	Total	100	100 %	100	100 %	10	100%	101	100 %		

[#] CLA - 4 can be from any combination of these: Assignments, Seminars, Tech Talks, Mini-Projects, Case-Studies, Self-Study, MOOCs, Certifications, Conf. Paper etc.,

Course Designers		
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